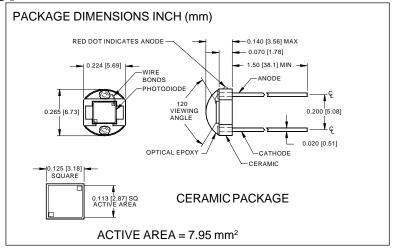
**PHOTONIC** Silicon Photodiode, U.V. Enhanced Photoconductive DETECTORS INC. Type PDU-C113





# **FEATURES**

- High speed
- Low capacitance
- U.V. enhanced
- Low dark current

# **DESCRIPTION**

The PDU-C113 is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive applications. Packaged on a two lead ceramic substrate with a clear U.V. epoxy glob top.

# **APPLICATIONS**

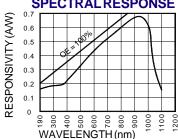
- U.V. exposure meter
- Water purification
- Fluorescence
- U.V. A & B meters

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V <sub>BR</sub>	Reverse Voltage		100	V	
T <sub>STG</sub>	Storage Temperature	-40	+100	∘C	
To	Operating Temperature Range	-40	+90	∘C	
Ts	Soldering Temperature*		+240	∘C	
IL	Light Current		0.5	mA	

<sup>\*1/16</sup> inch from case for 3 secs max

#### **SPECTRAL RESPONSE**



# ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	90	110		<b>m</b> A
ΙD	Dark Current	$H = 0$ , $V_R = 5 V$		5	30	nA
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	100	250		МΩ
TC Rsh	Rsн Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		%/℃
Cı	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		60		pF
λrange	Spectral Application Range	Spot Scan	250		1100	nm
λр	Spectral Response - Peak	Spot Scan		850		nm
VBR	Breakdown Voltage	I = 10 <b>m</b> A	50	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		9.0x10 <sup>-14</sup>		W/ √Hz
tr	Response Time	$RL = 1 K\Omega V_R = 50 V$		16		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f = 1 MHz